



**N - CHANNEL ENHANCEMENT MODE
POWER MOS TRANSISTORS**

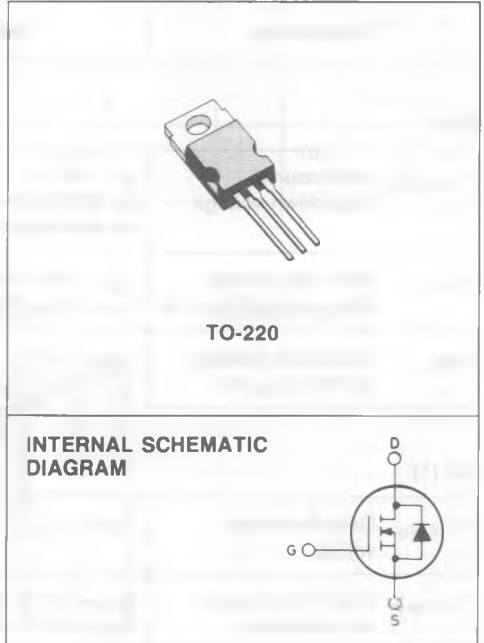
TYPE	V _{DSS}	R _{DS(on)}	I _D
SGSP321	60 V	0.13 Ω	16 A
SGSP322	50 V	0.13 Ω	16 A

- HIGH SPEED SWITCHING APPLICATIONS
- LOW VOLTAGE DC/DC CONVERTERS
- ULTRA FAST SWITCHING
- EASY DRIVE FOR REDUCED COST AND SIZE

INDUSTRIAL APPLICATIONS:

- SWITCHING POWER SUPPLIES
- MOTOR CONTROLS

N - channel enhancement mode POWER MOS field effect transistor. Easy drive and very fast switching times make this POWER MOS transistor ideal for high speed switching applications. Uses include motor speed control, low voltage DC/DC converters and solenoid driving.



ABSOLUTE MAXIMUM RATINGS

	SGSP321	SGSP322	
V _{DS}	60	50	V
V _{DGR}	60	50	V
V _{GS}		± 20	V
I _D	16		A
I _D	10		A
I _{DM} (*)	40		A
I _{DLM} (*)	40		A
P _{tot}	75		W
	Derating factor	0.6	W/°C
T _{stg}	- 65 to 150		°C
T _j	150		°C

(*) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj - case}$	Thermal resistance junction-case	max	1.67	°C/W
T_L	Maximum lead temperature for soldering purpose		275	°C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
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OFF

$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A$ for SGSP321 for SGSP322	$V_{GS} = 0$	60 50		V V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$	$T_c = 125^{\circ}C$		250 1000	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

$V_{GS (th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	$I_D = 250 \mu A$	2		4	V
$R_{DS (on)}$	Static drain-source on resistance	$V_{GS} = 10 V$ $V_{GS} = 10 V$	$I_D = 8 A$ $I_D = 8 A$			0.13 0.26	Ω Ω

DYNAMIC

g_{fs}	Forward transconductance	$V_{DS} = 25 V$	$I_D = 8 A$	3			mho
C_{iss}	Input capacitance	$V_{DS} = 25 V$ $V_{GS} = 0$	$f = 1 \text{ MHz}$		460	550	pF
C_{oss}	Output capacitance					350	pF
C_{rss}	Reverse transfer capacitance					180	pF

SWITCHING

$t_d (on)$	Turn-on time	$V_{DD} = 25 V$	$I_D = 8 A$		15	20	ns
t_r	Rise time	$V_i = 10 V$	$R_i = 4.7 \Omega$		45	60	ns
$t_d (off)$	Turn-off delay time	(see test circuit)			40	55	ns
t_f	Fall time				25	35	ns

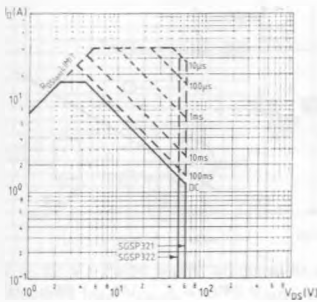
ELECTRICAL CHARACTERISTICS (Continued)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (*)$	Source-drain current Source-drain current (pulsed)			16 40	A A
V_{SD}	Forward on voltage	$I_{SD} = 16\text{ A}$	$V_{GS} = 0$	1.4	V
t_{rr}	Reverse recovery time	$I_{SD} = 16\text{ A}$ $di/dt = 25\text{ A}/\mu\text{s}$	$V_{GS} = 0$	100	ns

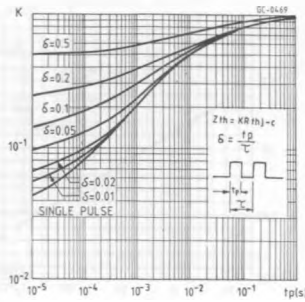
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

(*) Pulse width limited by safe operating area

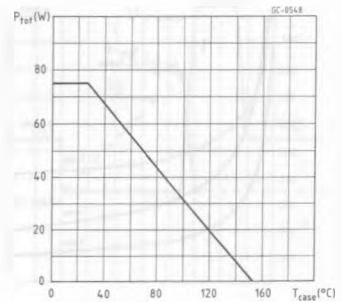
Safe operating areas



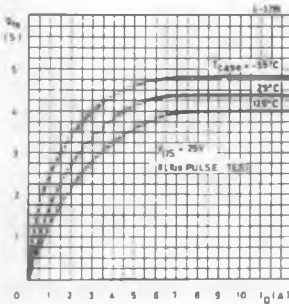
Thermal impedance



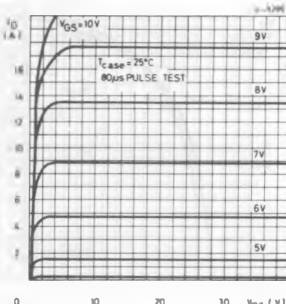
Derating curve



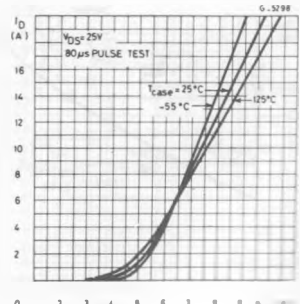
Output characteristics



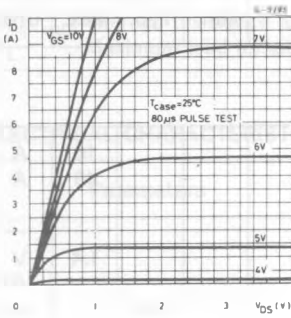
Output characteristics



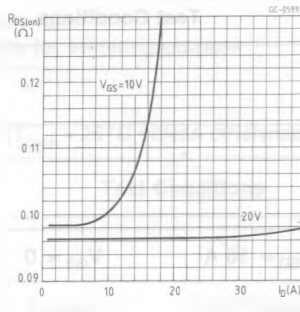
Transfer characteristics



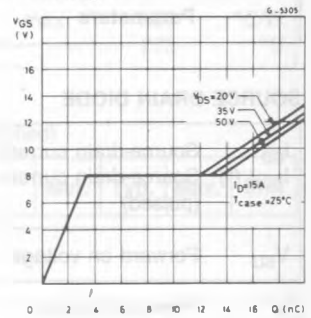
Transconductance



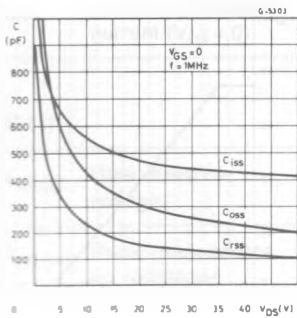
Static drain-source on resistance



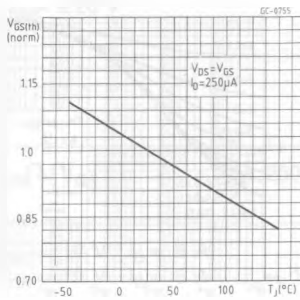
Gate charge vs gate-source voltage



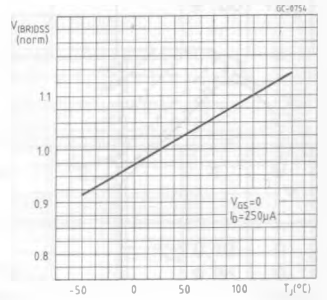
Capacitance variation



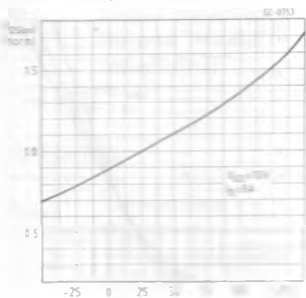
Normalized gate threshold voltage vs temperature



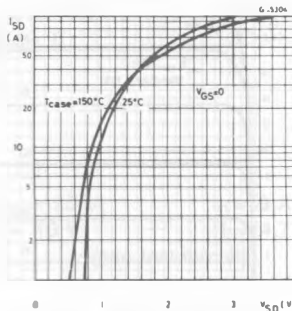
Normalized breakdown voltage vs temperature



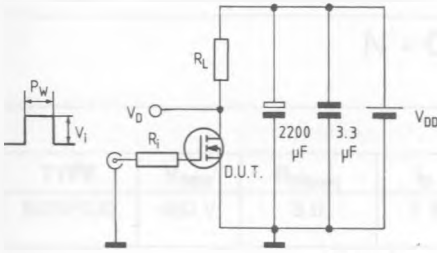
Normalized on resistance vs temperature



Source-drain diode forward characteristics



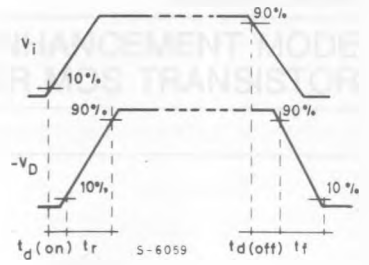
Switching times test circuit for resistive load



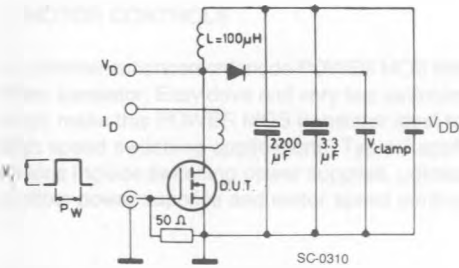
Pulse width $\leq 100 \mu\text{s}$
 Duty cycle $\leq 2\%$

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Switching time waveforms for resistive load



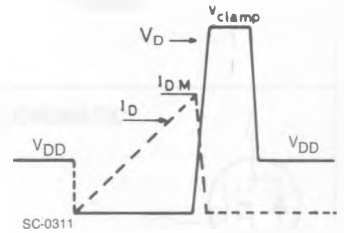
Clamped inductive load test circuit



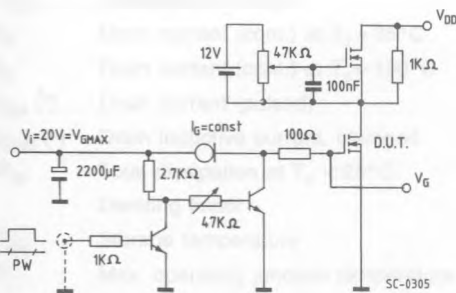
$V_i = 12 \text{ V}$ - Pulse width: adjusted to obtain specified I_{DM} . $V_{clamp} = 0.75 V_{(BR) DSS}$

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Clamped inductive waveforms



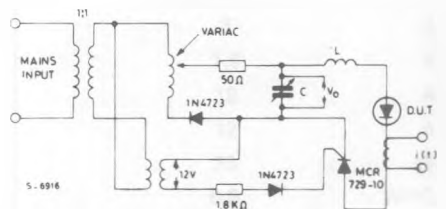
Gate charge test circuit



PW adjusted to obtain required V_G

SC-0305

Body-drain diode t_{rr} measurement
 Jedec test circuit



S-6916